

BFQ18A

NPN 4 GHz wideband transistor

Rev. 03 — 28 September 2007

Product data sheet

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NPN 4 GHz wideband transistor

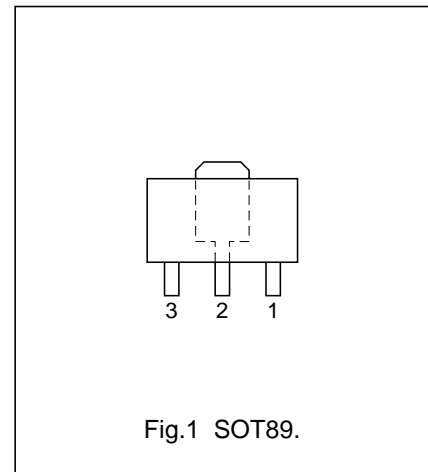
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DESCRIPTION

NPN transistor in a plastic SOT89 envelope intended for application in thick and thin-film circuits. It is primarily intended for MATV purposes.

PINNING

| PIN | DESCRIPTION |
|----------|-------------|
| Code: FF | |
| 1 | emitter |
| 2 | collector |
| 3 | base |



QUICK REFERENCE DATA

| SYMBOL | PARAMETER | CONDITIONS | TYP. | MAX. | UNIT |
|-----------|----------------------------|--|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | – | 25 | V |
| V_{CEO} | collector-emitter voltage | open base | – | 18 | V |
| I_C | DC collector current | | – | 150 | mA |
| P_{tot} | total power dissipation | up to $T_s = 155\text{ °C}$ (note 1) | – | 1 | W |
| f_T | transition frequency | $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 500\text{ MHz}$; $T_j = 25\text{ °C}$ | 4 | – | GHz |
| C_{re} | feedback capacitance | $I_C = 0$; $V_{CE} = 10\text{ V}$; $f = 10.7\text{ MHz}$ | 1.2 | – | pF |
| d_{im} | intermodulation distortion | $I_C = 80\text{ mA}$; $V_{CE} = 10\text{ V}$; $R_L = 75\text{ }\Omega$; $V_o = 700\text{ mV}$; measured at $f_{(p+q-r)} = 793.25\text{ MHz}$ | – | –60 | dB |

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|-----------|---------------------------|--------------------------------------|------|------|------|
| V_{CBO} | collector-base voltage | open emitter | – | 25 | V |
| V_{CEO} | collector-emitter voltage | open base | – | 18 | V |
| V_{EBO} | emitter-base voltage | open collector | – | 2 | V |
| I_C | DC collector current | | – | 150 | mA |
| P_{tot} | total power dissipation | up to $T_s = 155\text{ °C}$ (note 1) | – | 1 | W |
| T_{stg} | storage temperature | | –65 | 150 | °C |
| T_j | junction temperature | | – | 175 | °C |

Note

- T_s is the temperature at the soldering point of the collector tab.

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THERMAL RESISTANCE

| SYMBOL | PARAMETER | CONDITIONS | THERMAL RESISTANCE |
|---------------|---|--------------------------------------|--------------------|
| $R_{th\ j-s}$ | thermal resistance from junction to soldering point | up to $T_s = 155\text{ °C}$ (note 1) | 20 K/W |

Note

- T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

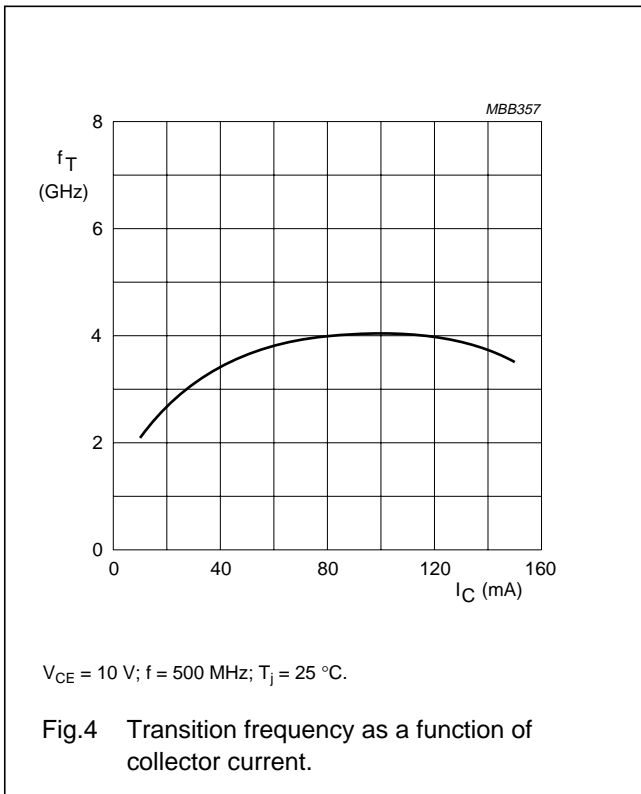
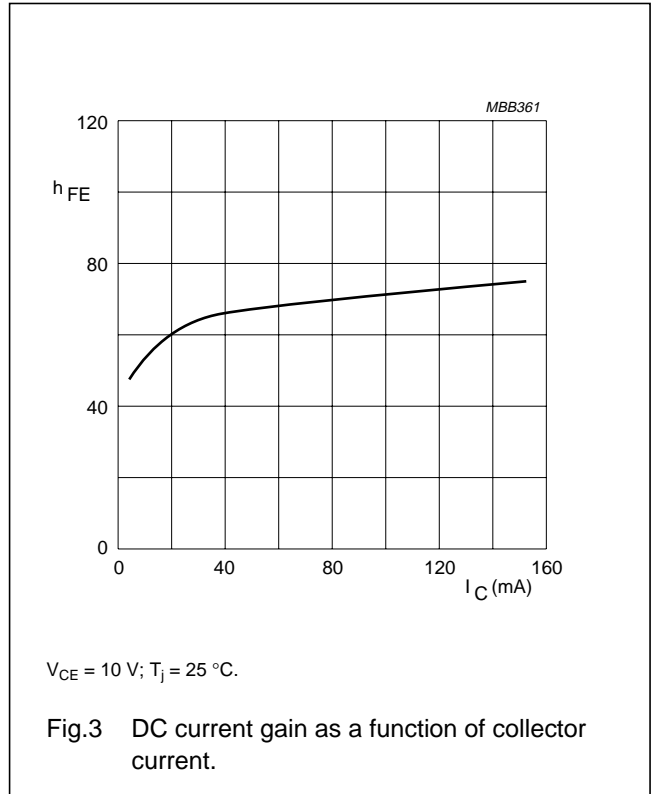
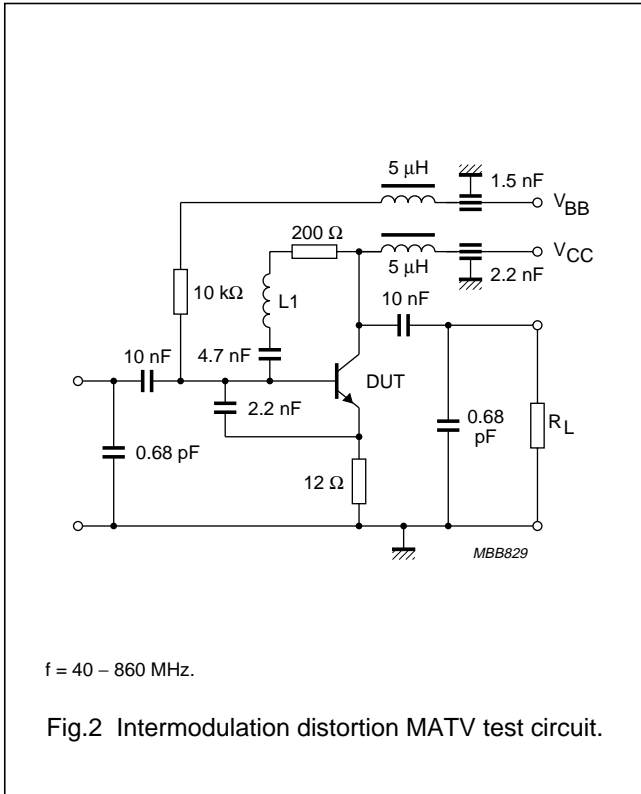
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | UNIT |
|----------|--|---|------|------|------|
| h_{FE} | DC current gain | $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$ | 25 | – | |
| C_c | collector capacitance | $I_E = i_e = 0$; $V_{CB} = 10\text{ V}$; $f = 1\text{ MHz}$ | – | 2 | pF |
| C_e | emitter capacitance | $I_C = i_c = 0$; $V_{EB} = 0.5\text{ V}$; $f = 1\text{ MHz}$ | – | 11 | pF |
| C_{re} | feedback capacitance | $I_C = 0$; $V_{CE} = 10\text{ V}$; $f = 10.7\text{ MHz}$ | – | 1.2 | pF |
| f_T | transition frequency | $I_C = 100\text{ mA}$; $V_{CE} = 10\text{ V}$; $f = 500\text{ MHz}$ | – | 4 | GHz |
| d_{im} | intermodulation distortion (see Fig.2) | note 1 | – | –60 | dB |

Note

- $I_c = 80\text{ mA}$; $V_{CE} = 10\text{ V}$; $R_L = 75\ \Omega$;
 $V_p = V_o = 700\text{ mV}$; $f_p = 795.25\text{ MHz}$;
 $V_q = V_o - 6\text{ dB}$; $f_q = 803.25\text{ MHz}$;
 $V_r = V_o - 6\text{ dB}$; $f_r = 805.25\text{ MHz}$;
measured at $f_{(p+q-r)} = 793.25\text{ MHz}$.

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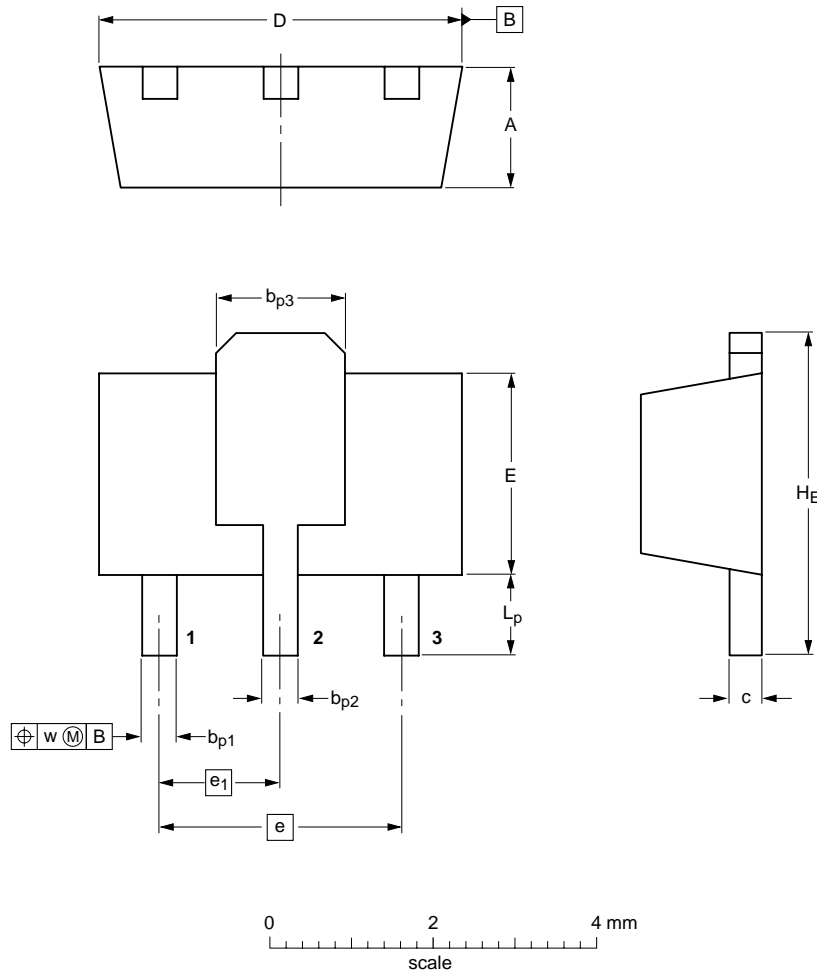
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PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

| UNIT | A | b _{p1} | b _{p2} | b _{p3} | c | D | E | e | e ₁ | H _E | L _p | w |
|------|-----|-----------------|-----------------|-----------------|------|-----|-----|-----|----------------|----------------|----------------|------|
| mm | 1.6 | 0.48 | 0.53 | 1.8 | 0.44 | 4.6 | 2.6 | 3.0 | 1.5 | 4.25 | 1.2 | 0.13 |
| | 1.4 | 0.35 | 0.40 | 1.4 | 0.23 | 4.4 | 2.4 | | | | | |

| OUTLINE VERSION | REFERENCES | | | EUROPEAN PROJECTION | ISSUE DATE |
|-----------------|------------|--------|-------|---------------------|----------------------|
| | IEC | JEDEC | JEITA | | |
| SOT89 | | TO-243 | SC-62 | | 06-03-16 06-08-29 |

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| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
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[2] The term 'short data sheet' is explained in section "Definitions".

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Revision history

Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------------------------------|-----------------------|---------------|--------------|
| BFQ18A_N_3 | 20070928 | Product data sheet | - | BFQ18A_CNV_2 |
| Modifications: | • Fig. 1 and package outline updated | | | |
| BFQ18A_CNV_2 | 19950901 | Product specification | - | - |

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